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CLAIM SET AS AMENDED:

1. (Currently Amended) A buffer formed between a substrate and a nitride semiconductor as a device material to be formed for constituting a device structure on said substrate, comprising:

a plurality of first layers made of a nitride semiconductor containing an impurity at a concentration of $1.2 \times 10^{20} \text{ cm}^{-3}$ - 10^{18} cm^{-3} or more and a plurality of second layers made of a nitride semiconductor containing no impurity, the first and second layers being laminated alternatively on each other and formed on the substrate to form a superlattice structure, and each of the second layers having a thickness substantially equal to four times a thickness of each of the first layers.

2. (Currently Amended) A buffer as claimed in claim 1 wherein:

the thickness of each of the first layers is substantially equal to 20 nm, and the thickness of each of the second layers is substantially equal to 80 nm, and

a concentration of the impurity contained in a nitride semiconductor for forming said first layer is 10% or less.

3. (Previously Presented) A buffer as claimed in any one of claims 1 and 2 wherein:

said impurity is Si (silicon), C (carbon), Mg (magnesium), or O (oxygen).